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Etching structures in etching body using plasma comprises coupling high frequency pulsed high frequency power with etching body using high frequency alternating voltage

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Patent Family:

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WO 200139261	A1	20010531	WO 2000DE3545	A	20001010	200148 B
DE 19957169	A1	20010613	DE 1057169	A	19991127	200148
EP 1153425	A1	20011114	EP 2000972618	A	20001010	200175
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			JP 2001540831	A	20001010	

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Abstract (Basic): WO 200139261 A1

NOVELTY - Etching structures in an etching body using a plasma comprises coupling a high frequency pulsed high frequency power with the etching body by means of an at least temporarily applied high frequency alternating voltage. The power is further modulated with a low frequency.

DETAILED DESCRIPTION - Preferred Features: The high frequency alternating voltage is prepared using a high frequency generator which produces a high frequency carrier signal. The high frequency pulsed high frequency power is pulsed with a frequency of 10-500, especially 50-200 kHz. The high frequency carrier signal has a frequency of 1-50, especially 13.56 MHz.

USE - For etching a silicon body.

ADVANTAGE - A higher etching rate is achieved.

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Title Terms: ETCH; STRUCTURE; ETCH; BODY; PLASMA; COMPRISE; COUPLE; HIGH; FREQUENCY; PULSE; HIGH; FREQUENCY; POWER; ETCH; BODY; HIGH; FREQUENCY; ALTERNATE; VOLTAGE

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